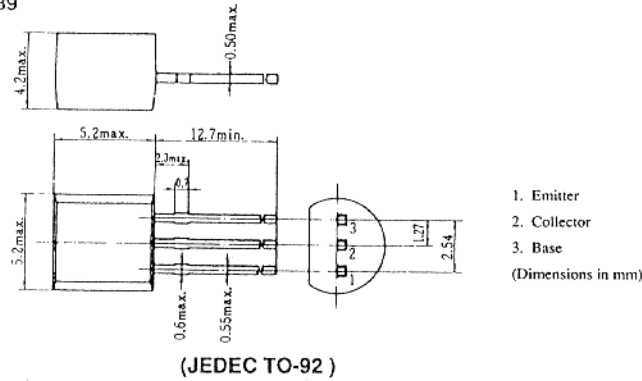


2SB1058

SILICON PNP EPITAXIAL

LOW FREQUENCY POWER AMPLIFIER

Complementary pair with 2SD1489

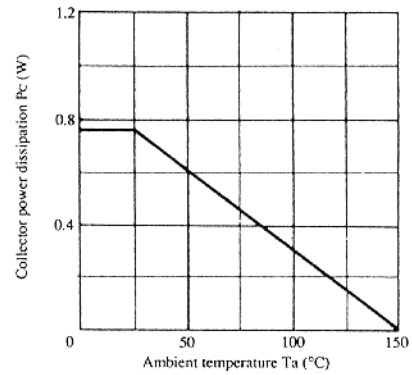


1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1058	Unit
Collector to base voltage	V _{CB0}	-20	V
Collector to emitter voltage	V _{CE0}	-16	V
Emitter to base voltage	V _{EB0}	-6	V
Collector current	I _C	-2	A
Collector power dissipation	P _C	0.75	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-20	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-16	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-6	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -16V, I _E = 0	—	—	-2	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -6V, I _C = 0	—	—	-0.2	μA
DC current transfer ratio	h _{FE} *	V _{CE} = -2V, I _C = -0.1A	100	—	320	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -1A, I _B = -0.1A	—	—	-0.3	V
Gain bandwidth product	f _r	V _{CE} = -2V, I _C = -10mA	—	80	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	50	—	pF

* The 2SB1058 is grouped by h_{FE} as follows.

B	C
100 to 200	160 to 320

■ See characteristic curves of 2SB738.